

# COPY

**PATENT****AMENDMENTS TO THE SPECIFICATION**

Please amend the title in all instances as follows:

**BIPOLAR TRANSISTOR WITH AN ULTRA SMALL SELF-ALIGNED POLYSILICON  
EMITTER AND METHOD OF FORMING THE SILICON GERMANIUM BASE OF THE  
TRANSISTOR**

Please amend the first paragraph on page 1 as follows:

~~The present application~~ This is a divisional application of Application Serial No. 09/994,293 filed on November 26, 2002, which is a continuation-in-part of Application Serial No. 09/882,740 filed June 15, 2001 by Abdalla Aly Naem for Bipolar Transistor with a Silicon Germanium Base and an Ultra Small Self-Aligned Polysilicon Emitter and Method of Forming the Transistor.

New (Div. of 09/994,293)  
PRELIMINARY AMENDMENT

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Attorney Docket No. 100-15120  
(P04976-P01-D01)